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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSV)

2SK2776

Chopper Regulator, DC–DC Converter and Motor Drive Applications

- Low drain-source ON resistance $R_{DS}(ON) = 0.75 \Omega$ (typ.)
- High forward transfer admittance $|Y_{fs}| = 7.0 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (max) \ (V_{DS} = 500 \ V)$
- Enhancement-mode : $V_{th} = 2.0 \sim 4.0 \text{ V} (V_{DS} = 10 \text{ V}, \text{I}_{D} = 1 \text{ mA})$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	500	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V _{DGR}	500	V	
Gate-source voltage		V _{GSS}	±30	V	
Drain current	DC (Note 1)	۱ _D	8	А	
	Pulse (Note 1)	I _{DP}	32	А	
Drain power dissipatio	n (Tc = 25°C)	PD	65	W	
Single pulse avalanche energy (Note 2)		E _{AS}	312	mJ	
Avalanche current		I _{AR}	8	А	
Repetitive avalanche e	energy (Note 3)	E _{AR}	6.5	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

Thermal Characteristics

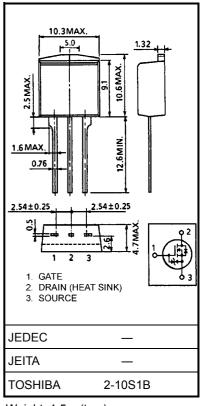
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch−c)}	1.92	°C / W
Thermal resistance, channel to ambient	R _{th (ch−a)}	83.3	°C / W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

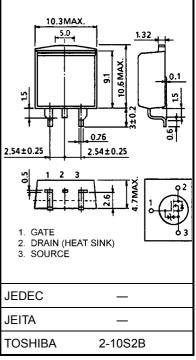
Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 8.3 mH, R_G = 25 Ω , I_{AR} = 8 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.



Weight: 1.5 g (typ.)



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Unit: mm

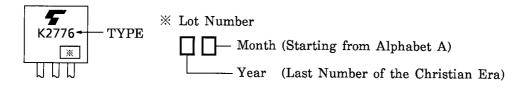
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V_{GS} = ±25 V, V_{DS} = 0 V	_	_	±10	μA
Gate-source br	eakdown voltage	V (BR) GSS	$I_{G} = \pm 10 \ \mu A, V_{DS} = 0 \ V$	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 500 V, V _{GS} = 0 V	_		100	μA
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	500	_	_	V
Gate threshold	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0		4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 4 A		0.75	0.85	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 4 A	3.5	7.0	_	S
Input capacitance C_{iss} Reverse transfer capacitance C_{rss} V_{DS} =				1300	_		
		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	130	_	pF
Output capacitance		Coss			400	_	
Switching time	Rise time	tr	$v_{GS} \stackrel{10V}{}_{0V} \int I_{D} = 4A$ $V_{OUT} \stackrel{V}{}_{CS} \stackrel{V}{}_{0V} \int I_{D} = 4A$ $R_{L} = 50\Omega$	_	26	_	
	Turn-on time	t _{on}		_	45	_	20
	Fall time	t _f		_	40	_	- ns
	Turn-off time	t _{off}	V_{DD} \Rightarrow 200V Duty \leq 1%, t _w = 10 μ s	_	140	_	
Total gate charge (gate-source plus gate-drain)		Qg		_	30	_	
Gate-source charge		Q _{gs}	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 80 A		17	_	nC
Gate-drain ("miller") Charge		Q _{gd}			13	_	

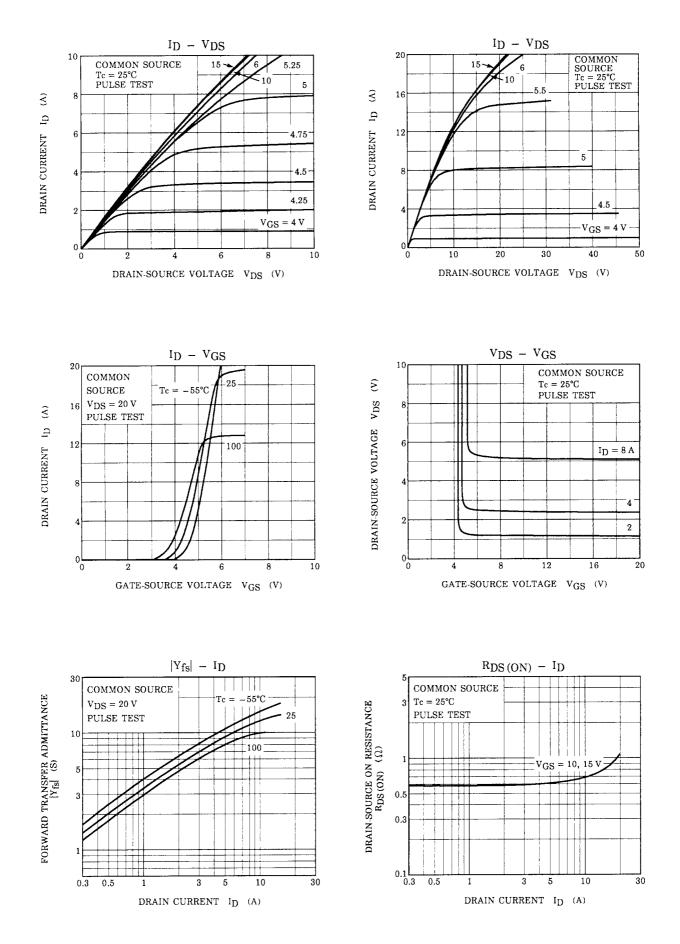
Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	8	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	32	A
Forward voltage (diode)	V _{DSF}	I _{DR} = 8 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 8 A, V _{GS} = 0 V, dI _{DR} / dt = 100 A / μs	—	1200	_	ns
Reverse recovery charge	Q _{rr}			12		μC

Marking

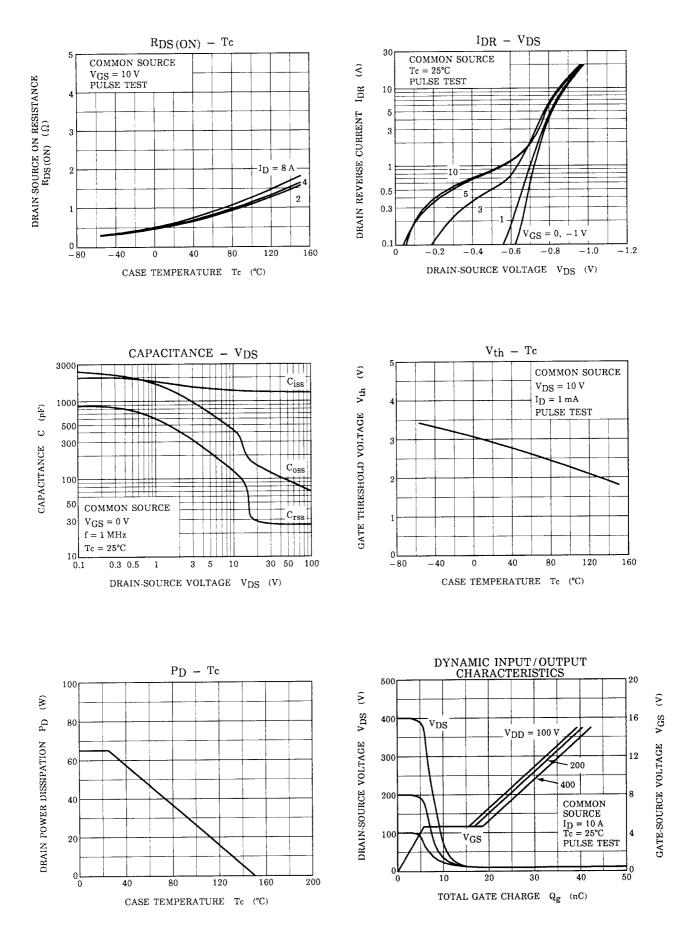


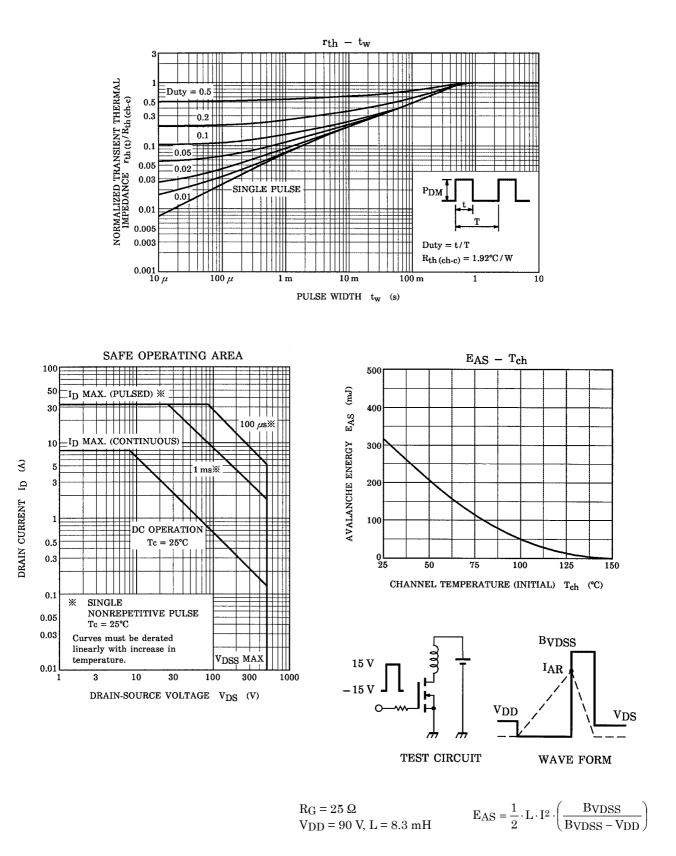
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2002-09-04

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